

ABSTRACT OF THE DISCLOSURE

A magnetoresistive effect sensor uses a shielded-type magnetoresistive effect element using a magnetoresistive effect film formed by a basic configuration of a combination of a free layer, a barrier layer formed on the free layer, and a fixed layer formed on the barrier layer, wherein a sensing current flows substantially perpendicular to the magnetoresistive effect film, and wherein an amorphous material or a microcrystalline material is used in a lower shield.

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